PETITION FO	R 1.136(a)	Docket No. LEE.009				
In Re Application ()f: Fuja Shone	FEB 10 2000	PEIGE OF			
Application No.	Filing Date 03/26/2004	Examined RADEMAR	Customer No. 20987	Group Art Unit 2812	Confirmation No.	
nvention: ONO	FORMATION METHO	OD				
his is a request ur	nder the provisions of 3	COMMISSIONER FOR PAT 37 CFR 1.136(a) to extend the identified application.		ng a response to	the Office Action	
he requested exte	<u></u>	neck time period desired): nths		nonths	Five months	
_	e amount of the fee is is hereby authorized t	\$120 and is to be pa s enclosed. so charge any fees which may		r credit any overp	payment, to	
any additiona		required, please consider the equired to Deposit Account N 0-2038 is attached		refor and charge		
WARNING:	Information on this f	orm may become public. Coredit card information and			not be	
DAM C. VOLENT	Signature FINE					
ÆG. NU. 33289	VOLENTINE FRANCOS & WHITT, PLLC ONE FREEDOM SQUARE 11951 FREEDOM DRIVE, SUITE 1260 RESTON VA 20190 TEL. (571) 283-0720			I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on		
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In re PATENT APPLICATION of

Mail Stop Amendment

Fuja Shone

Group Art Unit: 2812

Application No. 10/809,891

Examiner: Richard A. Booth

Filed March 26, 2004

Title: ONO FORMATION METHOD

RESPONSE TO ELECTION/RESTRICTION REQUIREMENT

U.S. Patent and Trademark Office Customer Service Window, Mail Stop Amendment Randolph Building 401 Dulany Street Alexandria VA 22314

Sir:

In response to the Office Action of December 10, 2004, Applicant elects the first embodiment (Figs. 3(a)-3(b)). Claims 1-5 read on the elected first embodiment, and claim 1 is generic to the elected first embodiment and the non-elected third embodiment (Figs. 5(a)-5(b)). The election is with <u>partial traverse</u>.

The first and third embodiments (Figs. 3 and 5, respectively) are both directed to a process in which a silicon-rich nitride layer is formed on a bottom oxide layer and is oxidized to form at least a portion of a top oxide layer of an ONO structure. The third embodiment differs from the first in that the third embodiment additionally includes deposition of an oxide layer on the silicon-rich layer prior to oxidation of the silicon-rich layer (see dependent claim 6). The first and third embodiments are not directed to mutually exclusive processes, and accordingly, these embodiments are not properly characterized as distinct species.

Applicants thus respectfully contend that the first and third embodiment constitute a single species, and that claims 1-10 read on this species of the invention.

Respectfully submitted,

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February 10, 2005

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